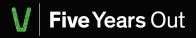
Vision Series: Power Management

International Rectifier

Driving Power Performance To The Next Level







Power designers continue to drive for higher performance and smaller size.

International Rectifier is a world leader in power management technology. IR's analog- and mixed-signal ICs, advanced circuit devices, integrated power systems, and components enable high-performance computing and reduce energy waste from motors, the world's single largest consumer of electricity.

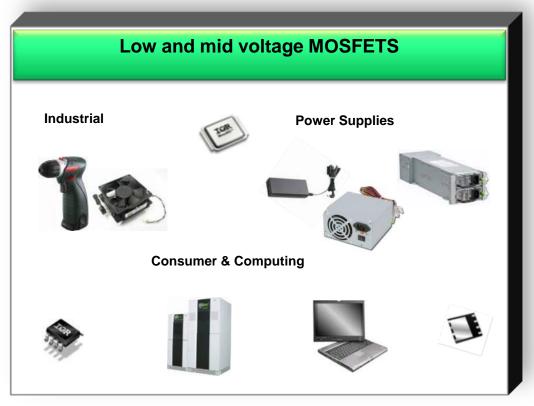
This review of current power management solutions and discussion of near term emerging materials demonstrates that IR is uniquely positioned with advanced technologies and packaging techniques to enable power designers to meet their size and efficiency challenges 5 year out







Designers must look carefully at the data sheet





- Low conduction losses low Rds(on).
 Application is normally Oring, Hot Swap, Motors, Battery protection
- Fast switching Low Figure of Merit (FOM)
 Rds x Qg. Application is normally DC-DC converters



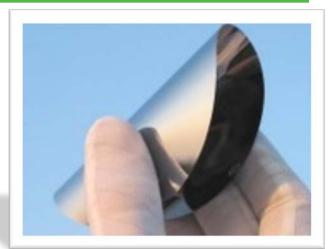


Power MOSFET Silicon Next Steps

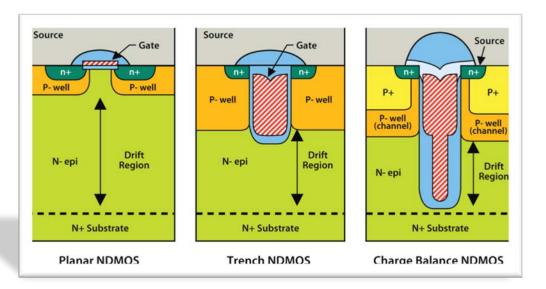


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- For low voltage MOSFETs Rds(on) can be reduced by thinning the wafer.
 - Bulk silicon is major contributor of Rds(on)
 - Thin wafers require specialized handling techniques



 New complex MOSFET structures utilize new wafer fab tools

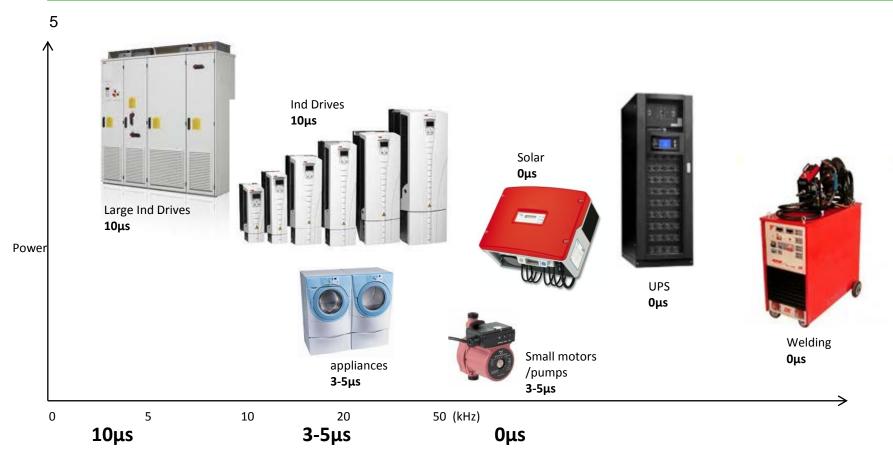






Application Specific IGBTs





Industrial Light Industrial/Consumer

Low switching frequency

IGBT Goal: Low Conduction losses & rugged operation

Requires: Short Circuit Capability & Low V_{CE(ON)}

Inductor on output

High switching frequency

IGBT Goal: Low switching losses

Requires: Low E_{TS}

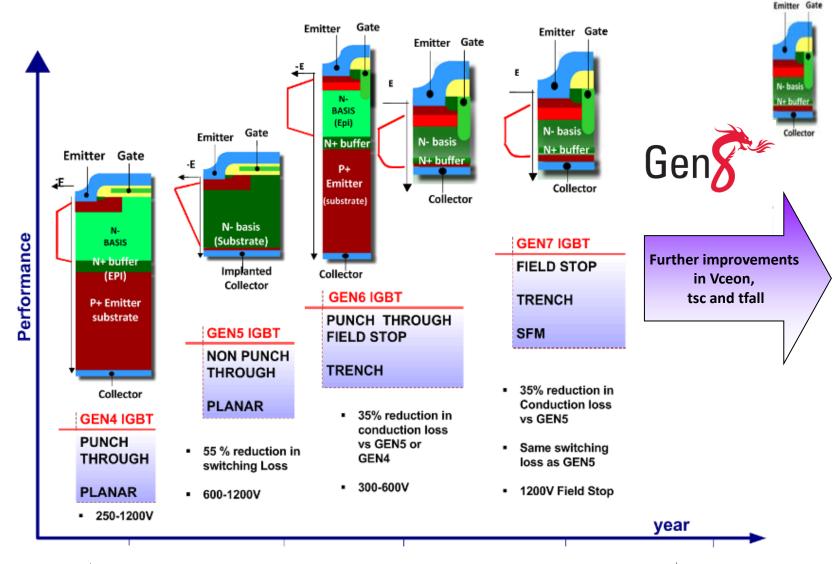




International Rectifier IGBT Platform Development







International Rectifier Trench IGBT Platforms



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Voltage	Туре	Speed	Applications	Characteristics
300V 330V	Epitaxial	U	PDP, Forklift, Welding	Very high peak current
600V 650V	Field Stop	K3	Appliance, UPS, Solar, Welding, PFC	High Frequency
		K6	Motor Drive	6 usec S.C.
	Epitaxial	U	PDP	Very high peak current
		F	Appliance	Fsw < 10 kHz
		S	50 or 60Hz	Very low Vceon
1200V	Field Stop	U	UPS, Welding, Solar, PFC	High Frequency
		K6	Electric Vehicle	6 usec S.C.
		K10	Motor Drive	10 usec S.C.

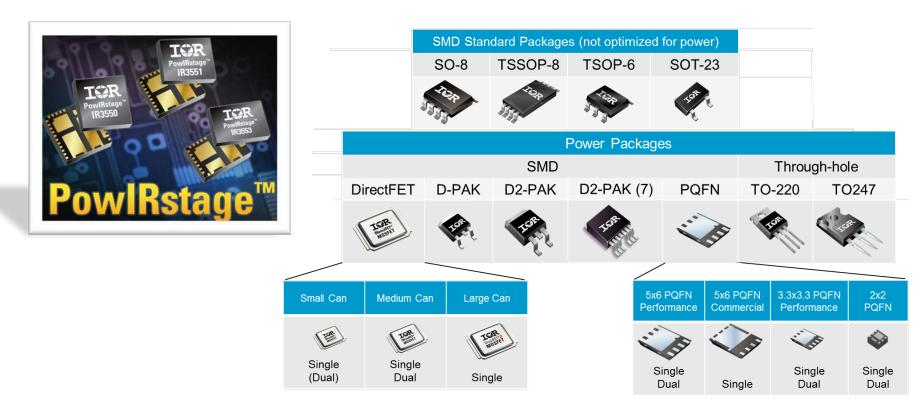
U=Ultrafast, F= Fast, S= Standard, K_x = Short Circuit x usec







Silicon improvements allow for smaller die sizes which in turn enables smaller packaging.



The packaging challenge

- Reduce the package resistance so the silicon Rds(on) improvements can be realized
- Increase the current handling capability





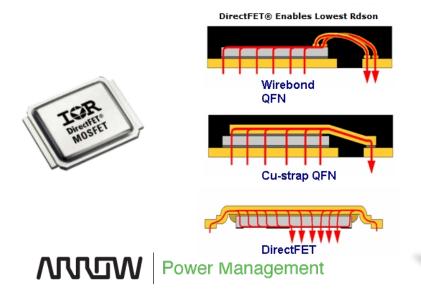


- Increase the pin count for higher current
 - 7 pins are better than 3!

Part#	Package	Rdson Max @ 10Vgs	Qg Typ	ld max
IRFS7430-7PPBF	D2PAK-7	.78 mOhm	300 <u>nC</u>	240A
IRFS7430PBF	D2PAK	1.3 mOhm	300 nC	195A

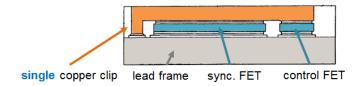
SMD					
D2-PAK	D2-PAK (7)				
TOP	Teach				

Remove the wirebonds



Dual Die Solution

IR is using a single clip to attach both dies:



Internal view from the side





Integration of Digital Control – Driving to ALL voltage rails





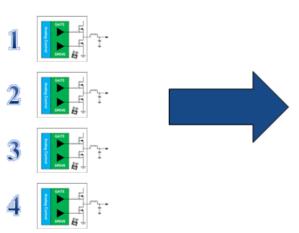


- Today Digital Control valued in high current Processor power solutions
 - Specific Processor power management interfaces (Intel SVID, others)
 - Non-linear performance for managing Transients (di/dt) and fast voltage changes (dv/dt)
 - Telemetry over I²C or PMBus reporting Voltage, Current, Efficiency, Temperature, etc
- Challenges going forward
 - More processors and devices need complex power management to manage power states (fast sleep, wakeup, power savings) → Even lower power devices need di/dt & dv/dt control
 - Processors are changing from 150W at 1.0V to multiple voltage rails (core, I/O, DDR, etc) that ALL need power controls
 - Telemetry accuracy is critical to manage performance even at lower currents

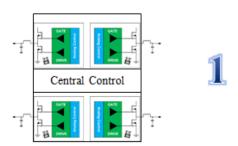




4 outputs today: 4 x DC/DC Converter



4 outputs tomorrow Single Multi-output IC



IR Solutions going forward

- Where today we offer Digital on Vcore, VDDR rails, IR will continue to develop digital solutions for every rail
 - Pure digital 100% digital control loop, telemetry, etc. More flexible
 - Hybrid Digital Analog control loop + Digital Wrapper: Lower Iq, simpler to use

IR Solutions – Related devices

- Intelligent Power Stages (Driver, High MOS, Low MOS) to contain Current sensing, temperature sensing, fault management
 - Plug-n-play solutions to create any complete system using combination of Monolithic digital power for lower current rails and multi-chip solutions for higher current rails

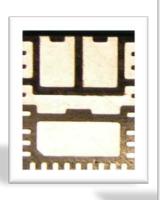


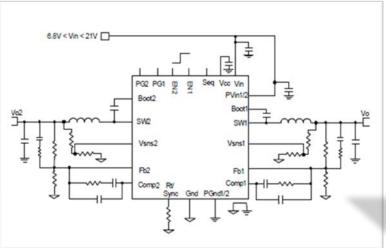


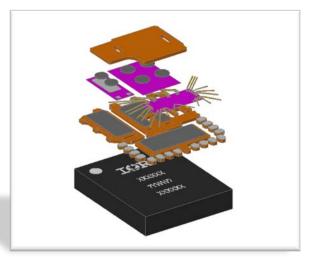
Multi-output Control - Managing Systems not Voltages



- ¹² Today IR provides high density leading DC/DC conversion for highly efficient, dense solutions
 - IR's SupIRbuck solutions are multichip Control IC + High MOS + Low MOS
 - Up to 2 voltages in a single device Dual Control + 2 x High MOS + 2 x Low MOS







Dual Output SupIRBuck

Single Output 25A SupIRBuck

- · Challenges going forward
 - To provide more than 2 voltages, multichip packaging becomes impossible (more than 5 die in a single package is not cost effective or size effective
 - Monolithic power Management ICs (PMICS) are in development
 - To be as efficient as IR's leading edge MOSFETs, a very low RDSon CMOS IC process is required

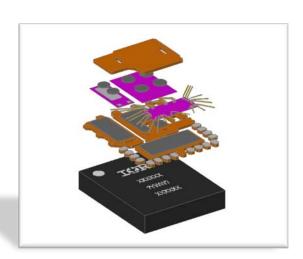




High Frequency – MOSFET & GaN based DC/DC



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- Today High Frequency switching driven by product Density
 - Efficiency vs Frequency vs Size continues to dominate Engineering Decisions
 - System/Power Engineers want to switch at least at 1MHz but power device Efficiency requires 400-800kHz
- Challenges going forward
 - Higher Efficiency Switching devices to reduce power losses, increase DC/DC converter efficiency
 - MOSFETs with Lower RDSon, Qg, Figure of Merit (FOM)
 Today's MOSFET RDSon is "package limited" where the wire bonds now dominate the RDSon
 - Continued wire-bond free packaging including copper clips, chipscale, etc.
 - Low voltage GaN devices to increase switching even further



– When MOSFETs and / or GaN get there, how to control the switch?

 $500kHz \rightarrow 1.5MHz \rightarrow 10-20MHz$

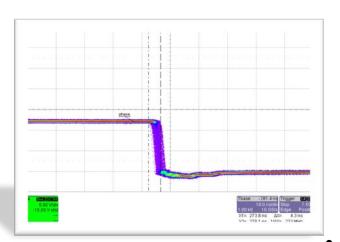




High Frequency – MOSFET & GaN based DC/DC



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12Vin 1Vout 1Mhz - 4.3ns Jitter

td(on)	Turn on delay	7.8ns
tr	Rise Time	8.9ns
td(off)	Turn off delay	9.3ns
tf Fall Time		5.3ns

The DC/DC Duty Cycle problem – 12V input, 1V output

- Today a DC/DC converter with 12V input 1V output → 10% duty cycle
 - At 1MHz, 10% duty cycle is a pulse width / on time of 100ns so VERY fast switching devices and control techniques used
 - At 10MHz, 10% duty cycle is a pulse width / on time of 10ns – by today's standards – this can't be done effectively today!

IR Solutions – Faster Analog Digital control & Faster devices

- In order to manage a 10-20MHz switching frequency, IR will continue to
 - Increase the speed of digital control but at the same time, continue to reduce quiescent current
 - Optimize Digital & Analog Use analog blocks for high speed and digital blocks for telemetry
 - Release next-generation MOSFETs and GaN devices to continue to drive higher efficiency solutions
 - Continue RoHS6 compatible packaging development to insure zero inductance solutions for higher frequency solutions





Key Differentiators

- Industry-leading analog HVICs and IGBT platforms
- Industry-leading energy saving design expertise
- Silicon packaging technology delivering superior system performance

Key Products

- Digital Control ICs
- High-Voltage ICs
- IGBTs
- IRAM Integrated Power Modules

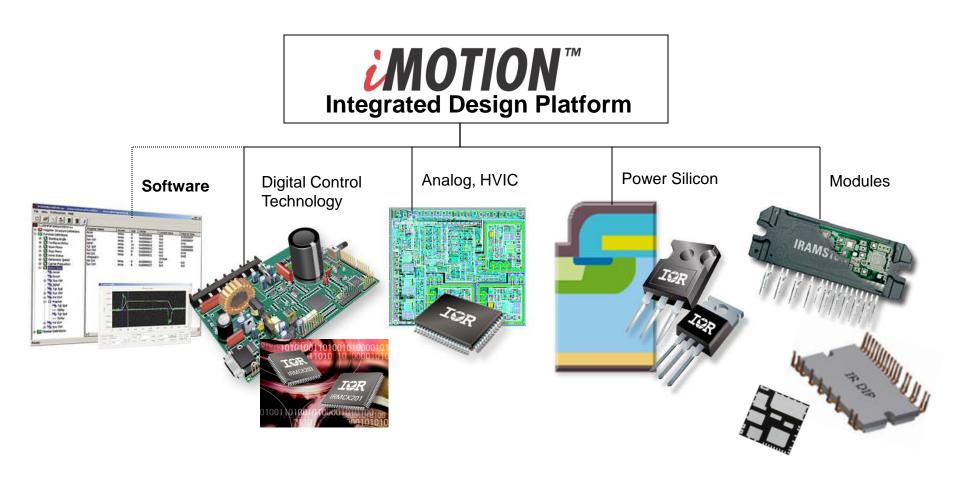










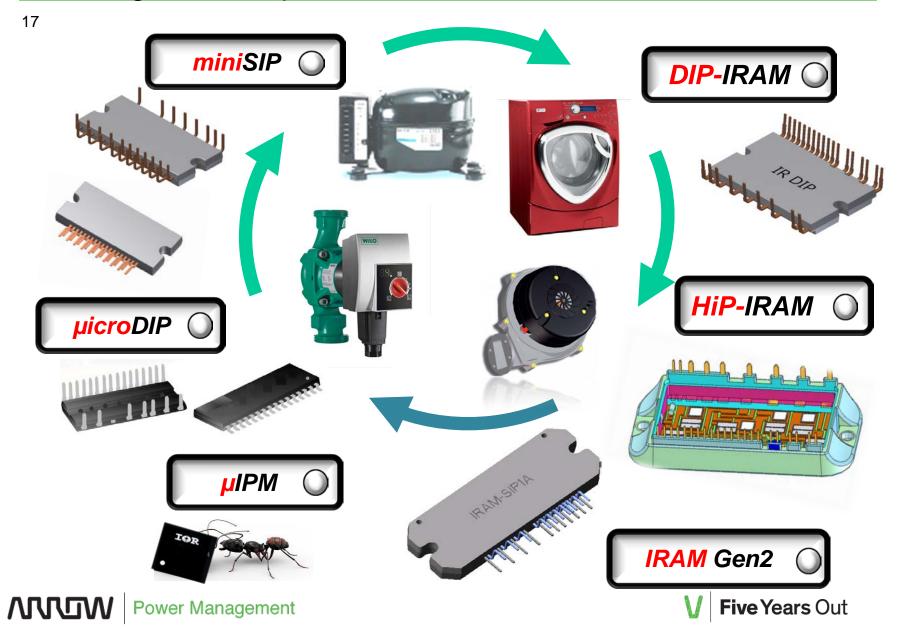






The Package Roadmap









- Up to 300W load management from a PQFN package
- Fully integrated ½-bridge &
- Full 3-phase Bridge motor control circuit solutions



The **µIPM**[™] Virtues

- 60% Smaller
- **No Heat Sink**
- Lower cost
- **Scalable Power**
- **Scalable Solutions**

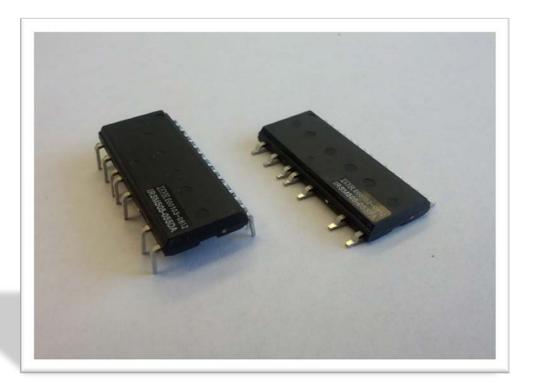


Integrated Power Module Package Expansion



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- Up to 300W load management with heatsink
- 3x HB configuration for simpler motor control circuit solutions
- IGBT based version available up to 3A-600V



*µicro*DiP Features

- Pin to Pin Compatible
- Standard Package
- Scalable Power
- Scalable Solutions



IPM Product Family Roadmap 2012~2015



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Launched at Electronica 2012

Half-Bridge



IR µIPM

- 300W+ ½ bridge IPM
- 500V, 6A 8A DC
- QFN 8 x 9



- · No heatsink, optional top side cooling
- Integrated bootstrap diode



Launched at PCIM 2012

- 30W 150W 3-phase IPM
- 250V/500V, 2A 4A DC
- QFN 12x12
- No heatsink
- Integrated bootstrap diode
- Overcurrent protection



· Pin to Pin compatible with existing IRAM

- **Exposed IMS substrate** improves thermal performance.
- 100% IR Owned design & manufacturing lines.





300W-500W 3-phase Smart IPM

IR DIP IRAM

- · 3-phase DIP-IPM
- 6~30A 600V
- Bootstrap Function



IR miniSiP & minDiP (SD-X)



- 250V/500V/600V
- Single 3 Phase HVIC, Bootstrap Function Built-in
- FREDFET & IGBT Version

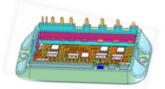




IR uicroDIP



- 250V/500V, 2A 5A DC
- DIP23 & SOP23
- 3 HB Drivers, Bootstrap Diode Function





 New 1200V & 600V **Industrial Modules**

Year

HV GaN Based μIPM^{m} ... What the Future Could Look Like



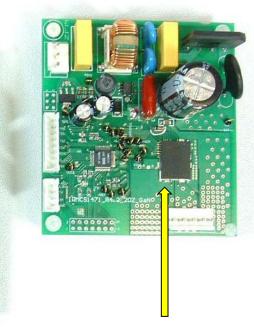
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400W Inverter Board for Appliance

IIIPM ™ GaN Based Prototype

6A IRAM with Heatsink





500V/160mohm **GaN in MCM** without Heatsink





Samsung 7.1 Channel Home Theater System



Model HT-F9750W features an IR Gallium Nitride powered amplifier that delivers pure sound





International Rectifier Your Power Management Partner Today & Five Years Out



For More Information:

Existing Arrow Customers: 800 777 2776

New Customers: 800 833 3557

www.arrownac.com/powermanagement



